



PATENT
Customer No. 22,852
Attorney Docket No. 07553.0029-00000

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
)
Masaaki HAGIHARA et al.) Group Art Unit: 1763
)
Application No.: 10/030,656) Examiner: A. Olsen
)
Filed: January 11, 2002)
)
For: ETCHING METHOD AND)
PLASMA PROCESSING)
METHOD)

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Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

AMENDMENT

In reply to the Office Action dated March 20, 2003, please amend the application as follows:

IN THE CLAIMS:

Please cancel claims 1-3 and 5 without prejudice or disclaimer, amend claims 4 and 6, and add new claim 12, as follows:

4. (Amended) An etching method for exposing a layer of Cu by etching a layer of SiN_x on the layer of Cu with an etching gas constituted of C, H, and F, wherein; said gas constituted of C, H, and F is CHF₃.